SEMICONDUCTOR

200mW SOD-323 SURFACE MOUNT Very Small Outline Flat Lead Plastic Package Schottky Barrier Diode

TAK CHEONG®

Absolute Maximum Ratings T _A = 25°C unless otherwise noted					
Symbol	Parameter	Value	Units		
PD	Power Dissipation	200	mW		
T _{STG}	Storage Temperature Range	-65 to +125	°C		
TJ	Operating Junction Temperature	+125	°C		
V _{RRM}	Repetitive Peak Reverse Voltage	30	V		
V _R	Maximum DC Blocking Voltage	30	V		
I _{F(AV)}	Average Forward Rectified Current	200	mA		
I _{FSM}	Peak Forward Surge Current	4	А		

These ratings are limiting values above which the serviceability of the diode may be impaired.

Specification Features:

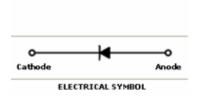
- Low Forward Voltage Drop
- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode

Electrical Characteristics $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Lir	Limits	
		Test Condition	Min	Max	Unit
Bv	Breakdown Voltage	I _R =10µA	30		Volts
I _R	Reverse Leakage Current	V _R =25V		2	uA
VF	Forward Voltage	I _F =0.1mA		0.24	
		I _F =1mA		0.32	
		I _F =10mA		0.40	Volts
		I _F =30mA		0.50	
		I _F =100mA		0.80	
T _{RR}	Reverse Recovery Time	I _F =I _R =10mA			
		$R_L=100\Omega$		5	nS
		I _{RR} =1mA			
С	Capacitance	V _R =1V, f=1M _{HZ}		10	pF

Freen	Product





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SOD-323 Flat Lead

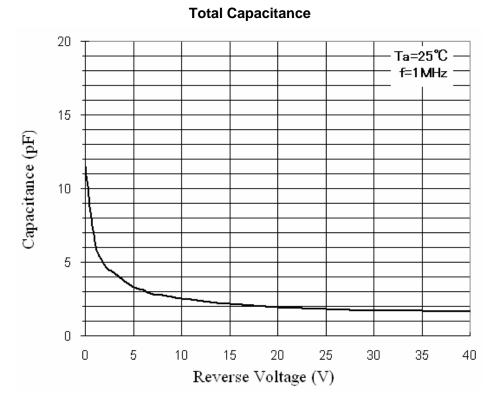
DEVICE MARKING CODES: Device Type Device Marking

BAT54WS

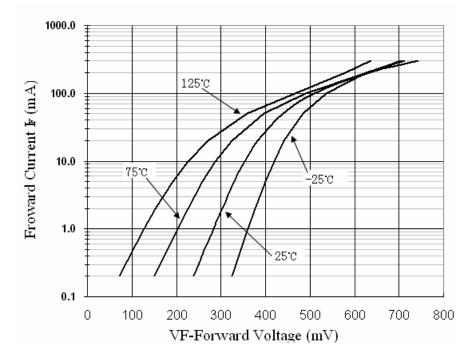


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Typical Performance Characteristics

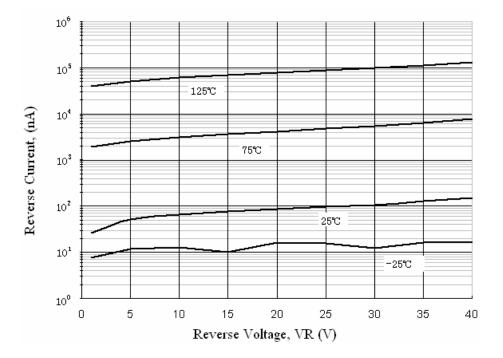


Forward Voltage vs Ambient Temperature



Nov 2008 Release, Revision C



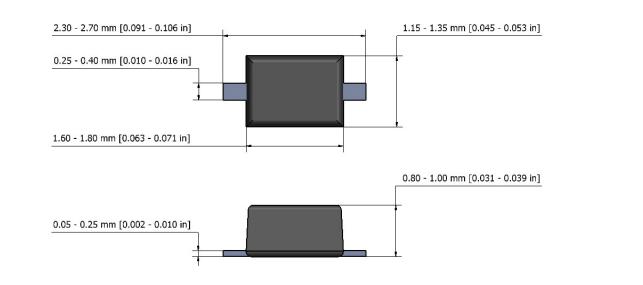


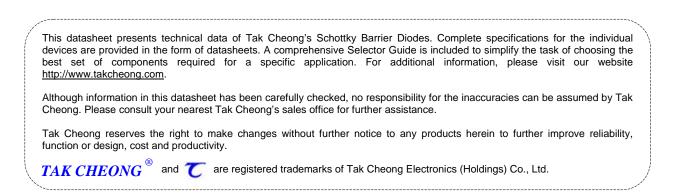
Reverse Current vs Reverse VoltageReverse



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SOD-323 Package Outline





Nov 2008 Release, Revision C